

/ Descriptions

TO-126F(R) PNP Silicon PNP transistor in a TO-126F(R) Plastic Package.

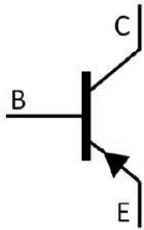
/ Features

Low $V_{CE(sat)}$, High V_{CEO} .

/ Applications

Low frequency power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

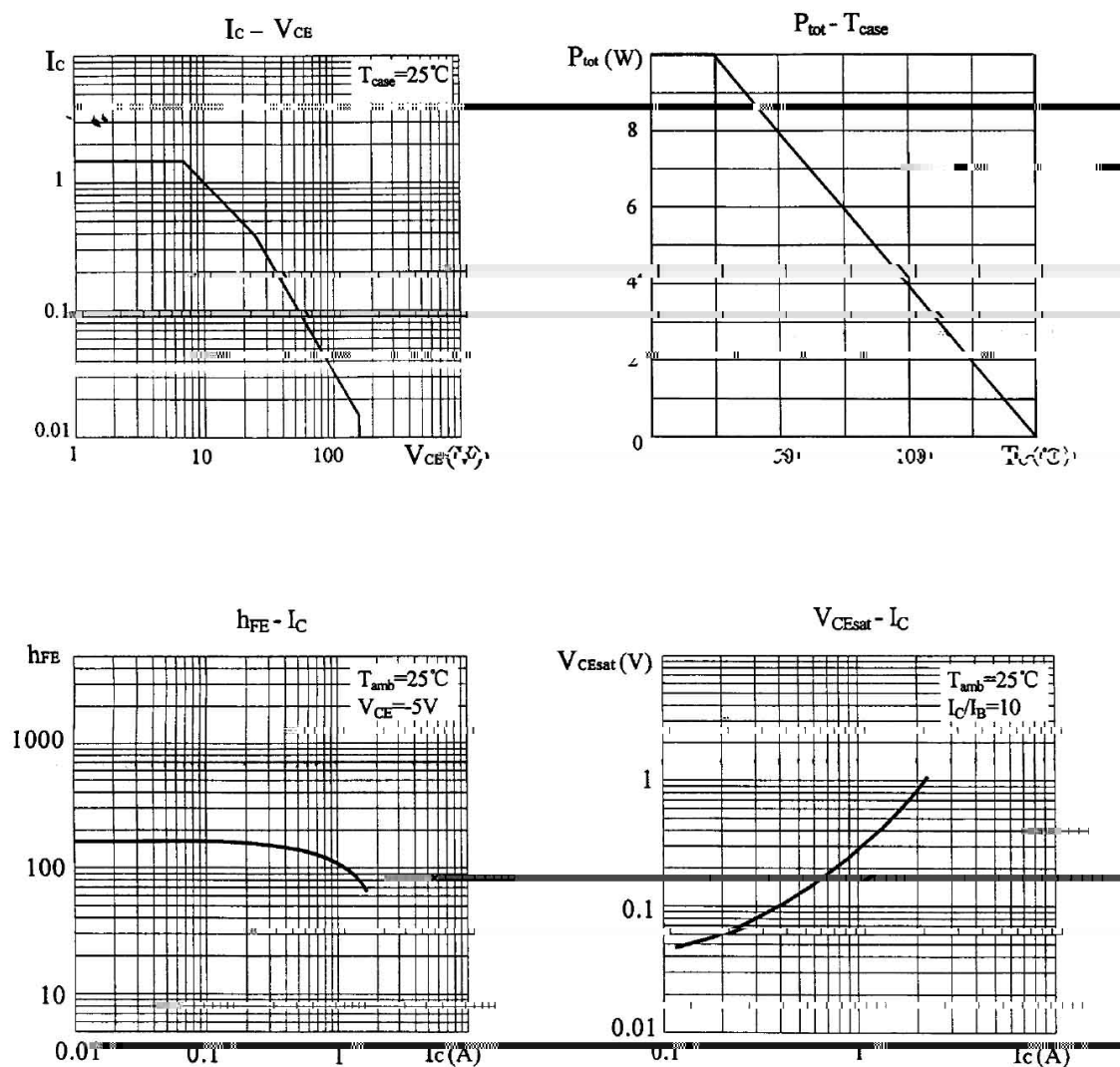
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O
h_{FE} Range	60~140	100~240

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-180	V
Collector to Emitter Voltage	V_{CEO}	-160	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter

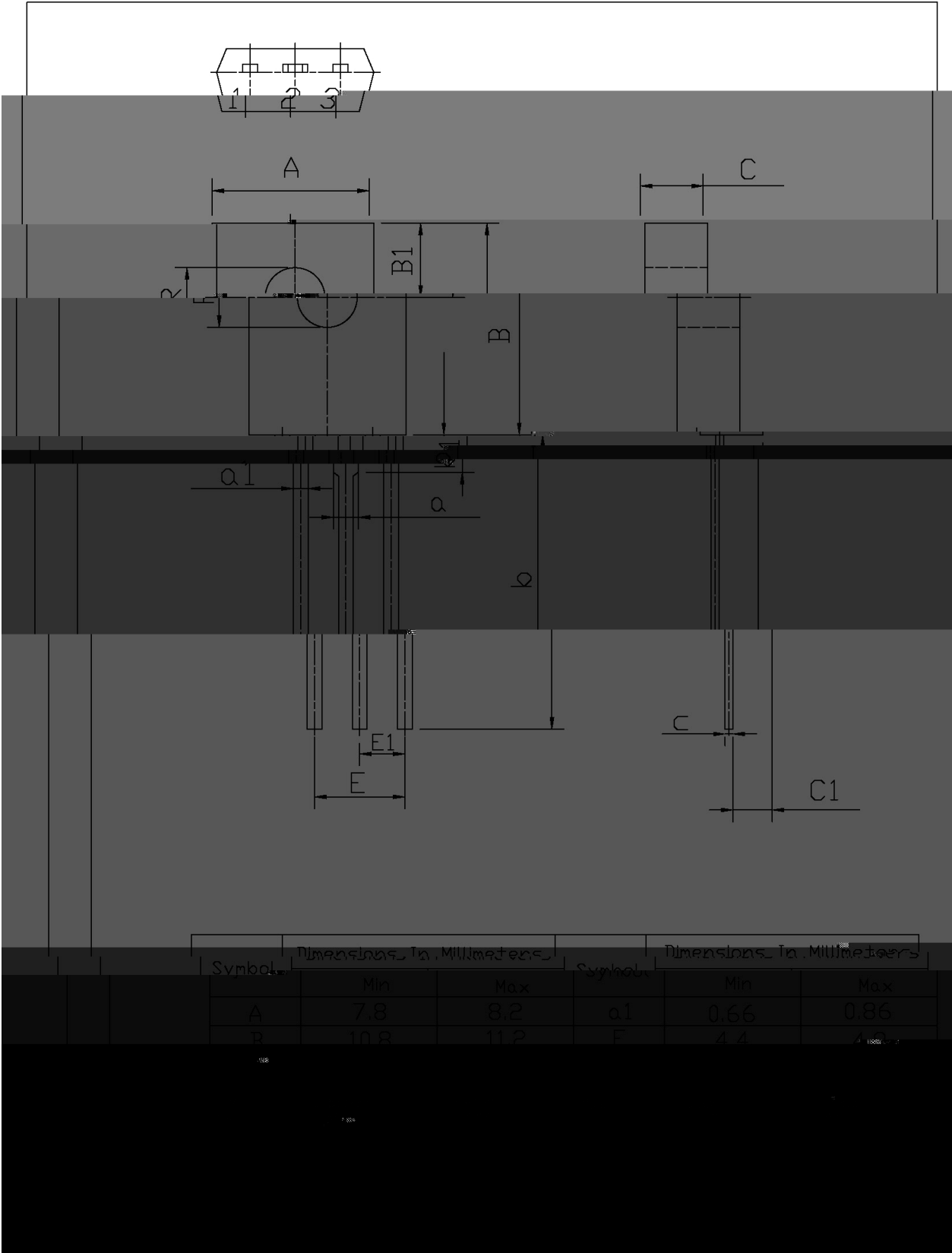
/ Electrical Characteristic Curve



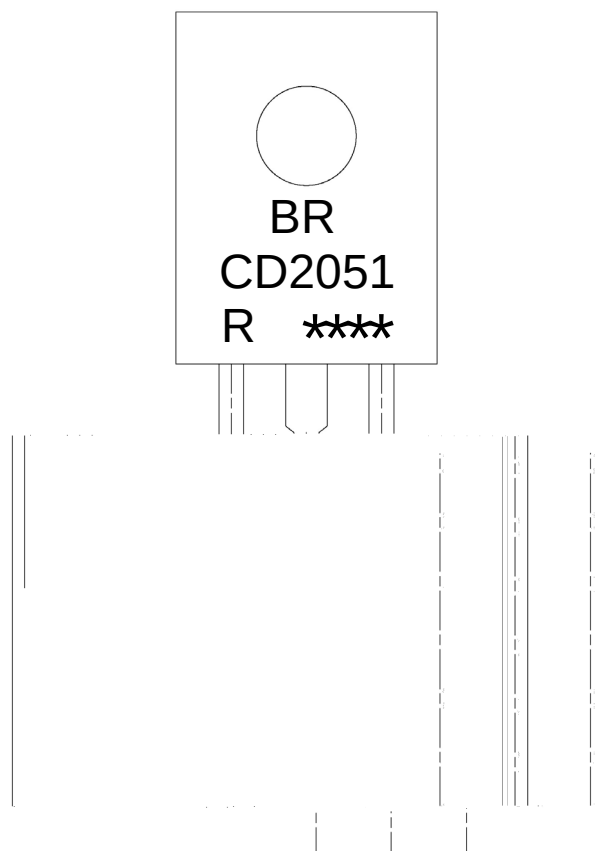
/ Package Dimensions

TQ-126F(R)

单位: mm



/ Marking Instructions



BR

CD2051

R: h_{FE}

Note:

BR: Company Code

CD2051: Product Type.

R: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;
- 3
- r 150

Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.